

ABSTRACT OF THE DISCLOSURE

A composition for etching and a method of manufacturing a semiconductor device, the method including an etching process of using the composition for etching, are
5 provided. The composition for etching includes a first inorganic acid; any one first additive selected from the group consisting of phosphorous acid, an organic phosphite, a hypophosphite, and mixtures thereof; and a solvent. The composition for etching is a high-selectivity composition for etching that can selectively remove a nitride film while minimizing the etch rate for an oxide film and does not have a problem such as particle
10 generation, which adversely affects device characteristics.

Representative drawing- FIG. 3